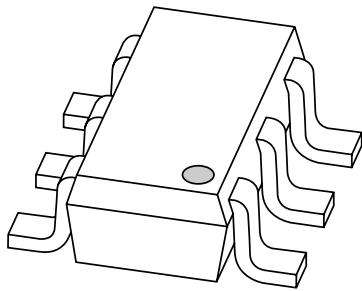


# DATA SHEET



## **PIMH9**

NPN resistor-equipped double  
transistor;  $R1 = 10\text{ k}\Omega$ ,  $R2 = 47\text{ k}\Omega$

Product specification

2001 Sep 13

# NPN resistor-equipped double transistor; R1 = 10 kΩ, R2 = 47 kΩ

**PIMH9**

**FEATURES**

- Transistors with built-in bias resistors (R1 typ. 10 kΩ and R2 typ. 47 kΩ)
- No mutual interference between the transistors
- Simplification of circuit design
- Reduces number of components and board space.

**APPLICATIONS**

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

**DESCRIPTION**

NPN resistor-equipped double transistor in an SC-74 (SOT457) plastic package.

**MARKING**

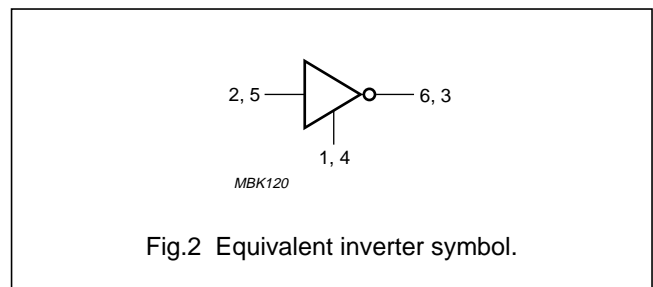
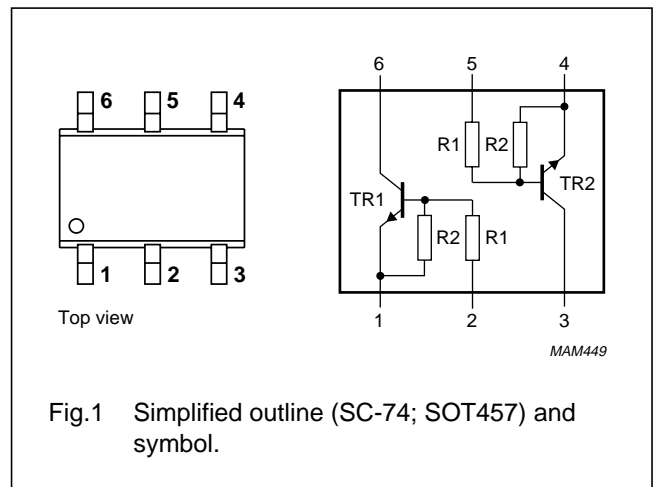
TYPE NUMBER	MARKING CODE
PIMH9	H9

**PINNING**

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2

**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	50	V
I <sub>CM</sub>	peak collector current	100	mA
R1	bias resistor	10	kΩ
R2	bias resistor	47	kΩ



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PIMH9

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	50	V
$V_{CEO}$	collector-emitter voltage	open base	–	50	V
$V_{EBO}$	emitter-base voltage	open collector	–	10	V
$V_I$	input voltage		–	+40	V
			–	–10	V
$I_O$	output current (DC)		–	100	mA
$I_{CM}$	peak collector current		–	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 1	–	300	mW
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$
$T_j$	junction temperature		–	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		–65	+150	$^\circ\text{C}$
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 1	–	600	mW

**Note**

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	208	K/W

**Note**

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

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PIMH9

### CHARACTERISTICS

$T_{\text{amb}} = 25 \text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per transistor</b>						
$I_{\text{CBO}}$	collector-base cut-off current	$V_{\text{CB}} = 50 \text{ V}$ ; $I_{\text{E}} = 0$	–	–	100	nA
$I_{\text{CEO}}$	collector-emitter cut-off current	$V_{\text{CE}} = 50 \text{ V}$ ; $I_{\text{B}} = 0$	–	–	1	$\mu\text{A}$
		$V_{\text{CE}} = 30 \text{ V}$ ; $I_{\text{B}} = 0$ ; $T_{\text{j}} = 150 \text{ }^\circ\text{C}$	–	–	50	$\mu\text{A}$
$I_{\text{EBO}}$	emitter-base cut-off current	$V_{\text{EB}} = 5 \text{ V}$ ; $I_{\text{C}} = 0$	–	–	150	$\mu\text{A}$
$h_{\text{FE}}$	DC current gain	$V_{\text{CE}} = 5 \text{ V}$ ; $I_{\text{C}} = 5 \text{ mA}$	100	–	–	
$V_{\text{CEsat}}$	saturation voltage	$I_{\text{C}} = 5 \text{ mA}$ ; $I_{\text{B}} = 0.25 \text{ mA}$	–	–	100	mV
$V_{\text{i(off)}}$	input off voltage	$V_{\text{CE}} = 5 \text{ V}$ ; $I_{\text{C}} = 100 \mu\text{A}$	–	0.7	0.5	V
$V_{\text{i(on)}}$	input on voltage	$V_{\text{CE}} = 0.3 \text{ V}$ ; $I_{\text{C}} = 1 \text{ mA}$	1.4	0.8	–	V
$R_1$	input resistor		7	10	13	$\text{k}\Omega$
$\frac{R_2}{R_1}$	resistor ratio		3.7	4.7	5.7	
$C_{\text{c}}$	collector capacitance	$I_{\text{E}} = i_{\text{e}} = 0$ ; $V_{\text{CB}} = 10 \text{ V}$ ; $f = 1 \text{ MHz}$	–	–	2.5	pF

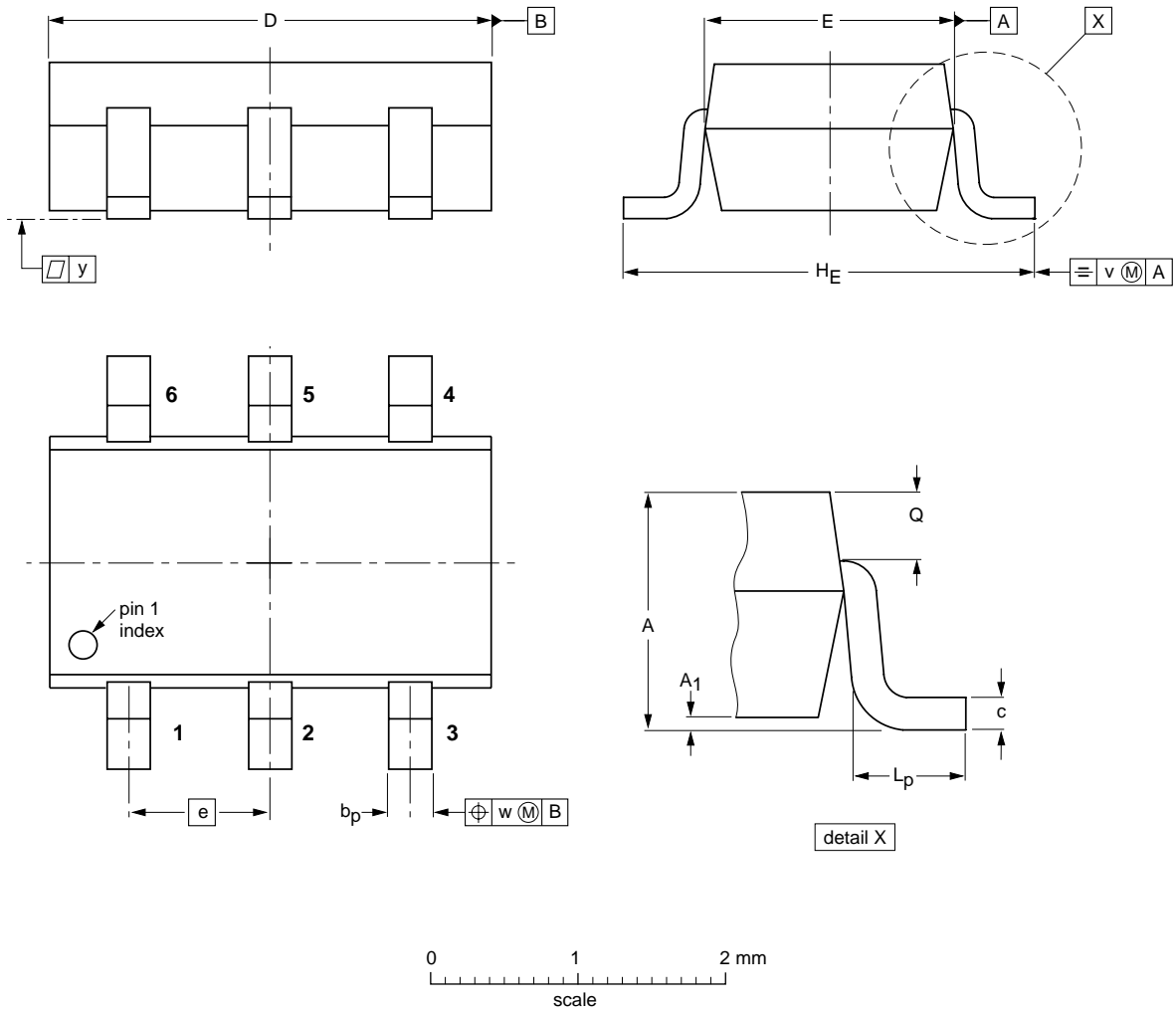
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PIMH9

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	c	D	E	e	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.1 0.9	0.1 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT457			SC-74			-97-02-28- 01-05-04

NPN resistor-equipped double transistor;  
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PIMH9

**NOTES**

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SCA73

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